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Claim 53 was rejected for being an incomplete sentence. In accordance with the Examiner's suggestion, claim 53 has been amended to recite "Ge-containing layer".

Claim 50 was rejected for reciting C as one of the possible groups from which X can be selected. Applicants respectfully note that C is recited as one option from which X can be selected.

The Examiner states that C is a member of group IVa of the periodic table. Based on the Periodic Table defined by the IUPAC, C is a member of group IVb. A copy of the IUPAC Periodic Table Applicants used is submitted herewith along with a copy of the Periodic Table from the CRC Handbook of Chemistry and Physics 75th ed. showing the new IUPAC notation, the previous IUPAC notation, and the CAS notation of the periodic groups. Withdrawal of the rejection is respectfully requested.

Claims 50-52, 55-58, 60 and 74 are rejected under 35 USC 102(b) as being anticipated by Yoshitomi et al. (JP 63-171453). This rejection is respectfully traversed.

Yoshitomi is directed to a magneto-optical recording medium and, thus, does not teach or suggest the phase-change recording layer of the present claims.

Claims 50-52, 55-58, 60 and 74 are rejected under 35 USC 102(b) as being anticipated by Kinou et al. (JP 03-248338). This rejection is respectfully traversed.

Claim 50 is directed to an optical information recording medium comprising a phase-change recording layer and a Ge-containing layer comprising either one selected from the group consisting of GeXN and GeXON. X is one or more elements selected from the following groups: IIIa, IVa, Va, VIa, VIII, Ib and IIb, and C.

Based on the IUPAC Periodic table used by the Applicants, the group to which Si belongs is not included. Thus, Kinou does not anticipate the claims by disclosing the use of GeSiZrN. Additionally, Kinou does not teach or suggest the phase-change recording layer of the present claims.

Claims 50-52, 55-58, 63, 64, and 74 are rejected under 102(b) as being anticipated by Yoshioka et al. (JP 04-052188). This rejection is respectfully traversed.

The rejection refers to the fact the Yoshioka discloses an SbGeTe recording layer. While the present invention does disclose a Ge-containing recording layer, based on the periodic table used by the Applicants, the present claims do not require the use of an SbGeTe

recording layer. Sb and Te are not members of any of the groups recited by the claims. Thus, Yoshioka fails to anticipate the claimed invention.

Claims 1, 2, 4-9, 12, 19-31, 50-52, 55-58, 63, 64, and 74 are rejected under 35 USC 102(b) as being anticipated by Yoshioka et al. (U.S. Patent 5,194,363). This rejection is respectfully traversed.

Yoshioka (US '363) discloses an SbGeTe recording layer which differs from the recording layer of the claimed invention. Unlike US '363, the claimed invention does not require a recording layer that includes Sb and Te.

Claims 50-52, 55-58, 60, and 74 are rejected under 35 USC 102(b) as being anticipated by Tsutsumi et al. (JP 02-037548), by JP 01-276453, by Shindo et al. (JP 05-274726), and by JP 04-069833. These rejections are respectfully traversed.

Tsutsumi, JP 01-276453, Shindo, and JP 04-06983 are all directed to a magneto-optical recording medium and, thus, does not teach or suggest the phase-change recording layer of the present claims.

Claims 1-9, 12, 19-31, 50-52, 55-58, 63, 64, and 74 are rejected under 35 USC 103(a) as being unpatentable over Yoshioka et al. (US '363) in view of Yoshioka et al. (JP 04-052188). This rejection is respectfully traversed.

The rejection states that it would have been obvious to one skilled in the art to provide a GeN or GeNO layer on both sides of the optical recording medium of US '363 based on the showing by JP 04-052188 that this layer is beneficial between the recording layer and the upper dielectric layer.

The combination of Yoshioka US '363 and Yoshioka JP 04-052188 does not suggest at the claimed invention as neither reference teaches or suggest a barrier layer including GeN or GeNO and at least one of the following elements: Al, B, Ba, Bi, C, Ca, Ce, Cr, Dy, Eu. Ga, Hf, In, K, La, Mn, Nb, Ni, Pb, Pd, Si, Sn, Ta, Ti, V, W, Yb, Zn, and Zr.

Furthermore, Yoshioka JP 04-052188 defines the optical recording medium as being comprised of a first dielectric layer, a record thin film, a nitride layer, a second dielectric layer, and a reflecting layer. The record film layer of JP 04-052188 is analogous to the active layer of US '363. Yoshioka JP 04-052188 does not teach or suggest a GeN or a GeNO layer on both sides of the recording medium.

Claims 1-31, 50-64 and 74 are rejected under 35 USC 103(a) as being unpatentable over Yoshioka et al. (US '363) in view of Yoshioka et al. (JP 04-052188) and either Yoshitomi et al. (JP 63-171453), Kinou et al. (JP 03-248338), or Shindo et al. (JP 05-274726). This rejection is respectfully traversed.

The rejection states that it would have been obvious to include additives, such as Al, Si, H, and Zr into the GeN and GeNO protective layers of the invention of Yoshioka US '363 as modified by Yoshioka JP 04-052188, based upon the disclosure of equivalent function as protective layers within either Yoshitomi, Kinou, or Shindo.

Yoshioka discloses an optical information recording medium comprising a substrate, a first dielectric layer, an active layer formed on top of the first dielectric layer, a second dielectric layer formed on top of the active layer, and a reflecting layer formed on top of the second dielectric layer (col. 3, lines 31-46). The active layer is a phase change material capable of absorbing energy and being converted between a substantially amorphous state and a substantially crystalline state (abstract).

From this disclosure it is evident that the active layer of US '363 is equivalent to the recording layer and not the barrier layer of the claimed invention. US '363 does not include a barrier layer as part of the recording medium structure. US '363 does disclose two dielectric layers sandwiching the active layer which could possibly be construed as protective layers, however their composition is disclosed as being a combination of ZnS or SiO₂ as opposed to GeN or GeNO as the rejection has suggested.

Additionally, Yoshioka JP 04-052188, as discussed previously, does not teach or suggest a protective layer comprising GeN or GeNO being included on either side of the recording medium. The combination of Yoshioka US '363 and Yoshioka JP 04-052188 does not suggest at the claimed invention. Furthermore, Yoshitomi, Kinou, or Shindo do not remedy this deficiency. Applicants do not concede the applicability of Yoshitomi, Kinou, or Shindo to claims 1-31, 50-64 and 74.

Claims 1-31, 50-64, and 74 are rejected under the judicially created doctrine of obviousness-type double patenting as being unpatentable over claims 22-33 of U.S. Patent 5,914,214. This rejection is respectfully traversed.

Applicants provide below a Terminal Disclaimer under 37 CFR 1.321(c) obviating the double patenting rejection. Applicants do not concede the correctness of the reasoning of the rejection.

Claims 1-31, 50-64, and 74 are provisionally rejected under the judicially created doctrine of obviousness-type double patenting as being unpatentable over claims 1-12, 14-15, 25-27, 30-42, and 54-55 of co-pending Application No. 09/050,762. This rejection is respectfully traversed. Applicants note that Application No. 09/050,762 is not issuing.

TERMINAL DISCLAIMER

Petitioner, Matsushita Electric Industrial Co., Ltd., the owner of the entire right, title and interest in the present application filed on September 30,1999 by virtue of Assignment recorded at Reel 010432, Frame(s) 0867 and U.S. Patent 5,914,214, through the undersigned attorney of record, hereby disclaims, except as provided below, the terminal part of the statutory term of any patent granted on the above-identified application, which would extend beyond the expiration date of the full statutory term of the patent to issue from U.S. Patent No. 5,914,214 and hereby agrees that any patent so granted on the above-identified application shall be enforceable only for and during such period that the legal title to said patent shall be the same as the legal title to the patent to issue from U.S. Patent No. 5,914,214, this agreement to run with any patent granted on the above-identified application and to be binding upon the grantee, its successors, or assigns.

In making the above disclaimer, Petitioner does not disclaim the terminal part of any patent granted on the above-identified application that would extend to the full statutory term as presently shortened by any terminal disclaimer of the patent to issue from U.S. Patent No. 5,914,214 in the event that any such issued patent: expires for failure to pay a maintenance fee, is held unenforceable, is found invalid, is statutorily disclaimed in whole or terminally

disclaimed under 37 CFR 1.321(a), has all claims cancelled by a reexamination certification, or is otherwise terminated prior to the expiration of its full statutory term as presently shortened by any terminal disclaimer, except for the separation of legal title stated above.

For submissions on behalf of an organization (e.g. corporation, partnership, university, government agency, etc.), the undersigned (whose title is supplied below) is empowered to act on behalf of the organization.

I hereby declare that all statements made herein of my own knowledge are true and that all statements made on information and belief are believed to be true; and further that these statements were made with the knowledge that willful false statements and the like so made are punishable by fine or imprisonment, or both, under Section 1001 of Title 18 of the United States Code and that such willful false statements may jeopardize the validity of the application or any patent issued thereon.

In Conclusion

In view of the above, favorable reconsideration is requested in the form of a Notice of Allowance.

Respectfully Submitted,

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John J. Gresens

Reg. No. 33,112

JJG/CDS

Dated 10/19/2000



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The new IUPAC format numbers the groups from 1 to 18. The previous IUPAC numbering system and the system used by Chemical Abstracts Service (CAS) are also shown. For radioactive elements that do not occur in nature, the mass number of the most stable isotope is given in parentheses.

REFERENCES

- 1. G. J. Leigh, Editor, Nomenclature of Inorganic Chemistry, Blackwells Scientific Publications, Oxford, 1990. 2. Chemical and Engineering News, 63(5), 27, 1985.